



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Features

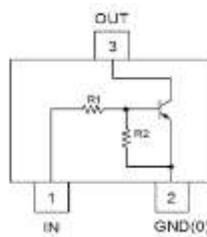
- Epitaxial Planar Die Construction
- Built-In Biasing Resistors,  $R1 = R2$

<b>R1, R2 (NOM)</b>
47k $\Omega$

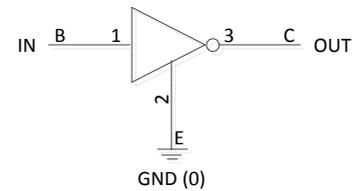
SOT23



Top View



Device Schematic



Equivalent Inverter Circuit

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

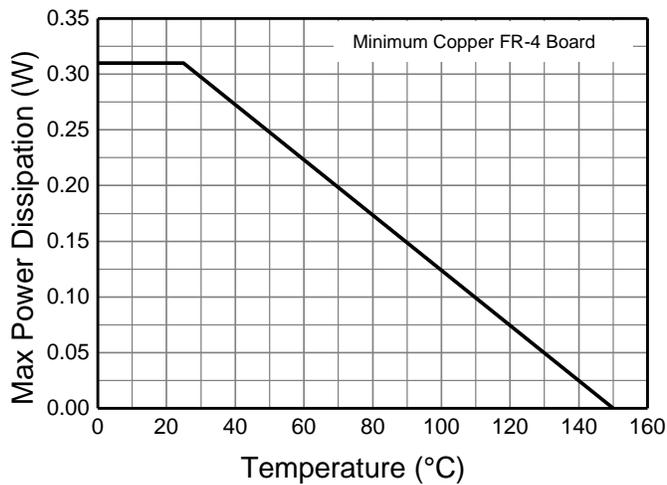
Characteristic	Symbol	Value	Unit
Supply Voltage <Pin: (3) to (2)>	V <sub>CC</sub>	-50	V
Input Voltage <Pin: (1) to (2)>	V <sub>IN</sub>	+10 to -40	V
Output Current	I <sub>O</sub>	-30	mA
Output Current	I <sub>C</sub> (Max)	-100	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

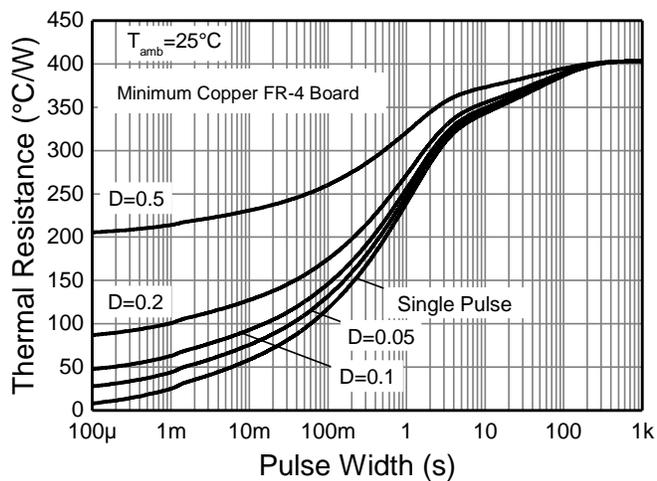
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	310	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	R <sub>θJA</sub>	403	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Note: 6. Mounted on FR-4 PC Board with minimum recommended pad layout.

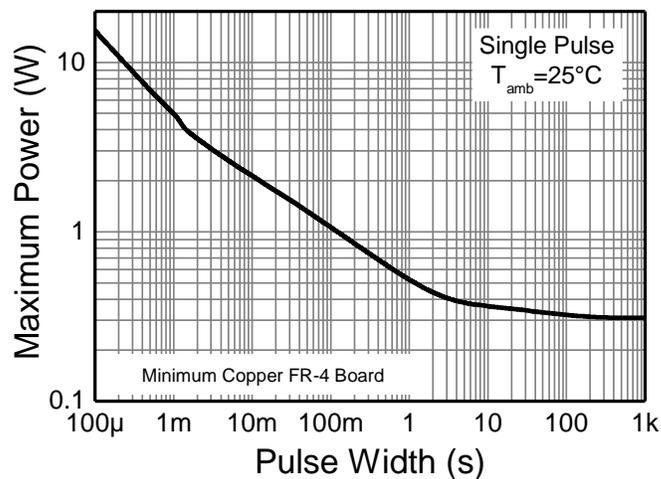
### Thermal Characteristics and Derating Information



**Derating Curve**



**Transient Thermal Impedance**



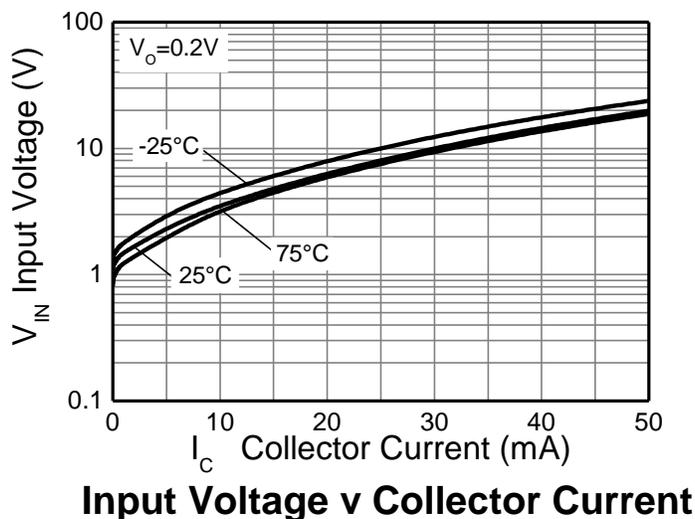
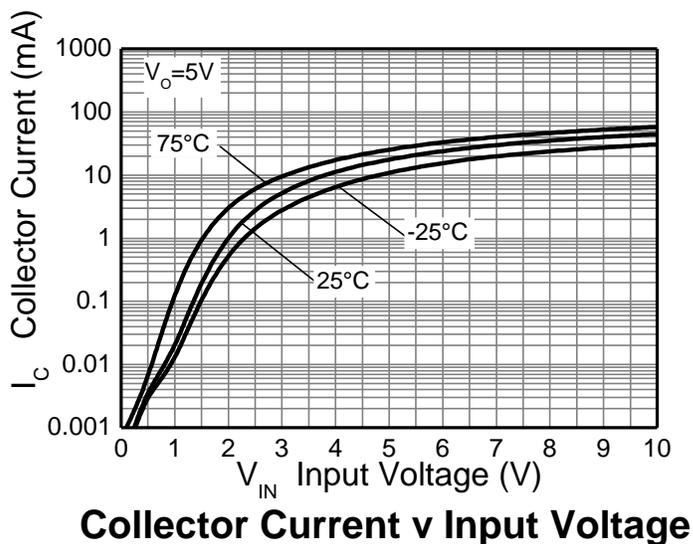
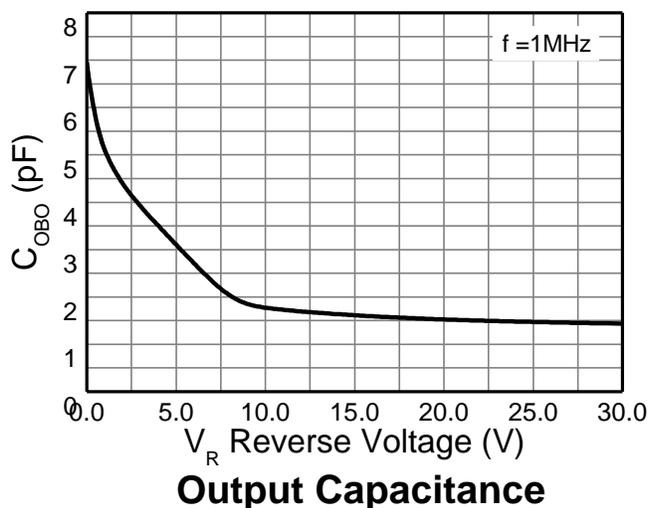
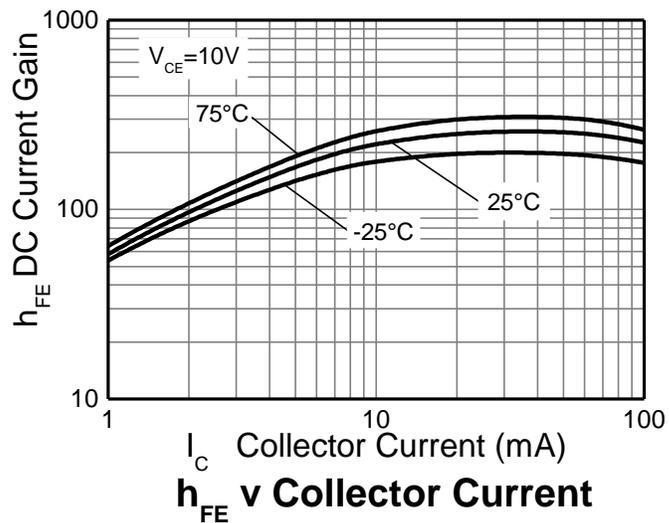
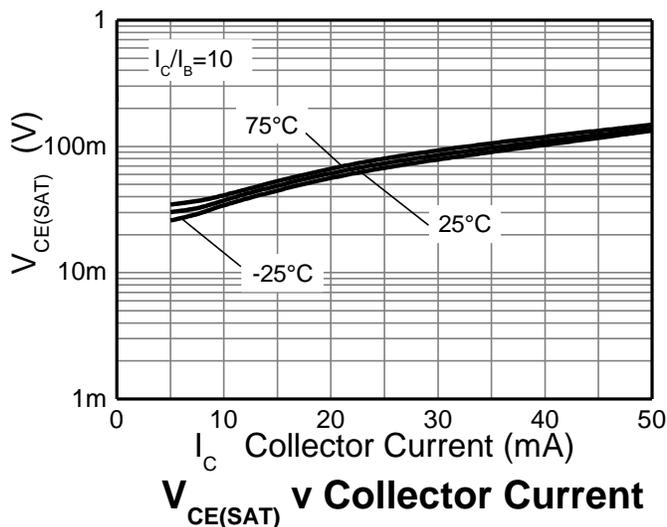
**Pulse Power Dissipation**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

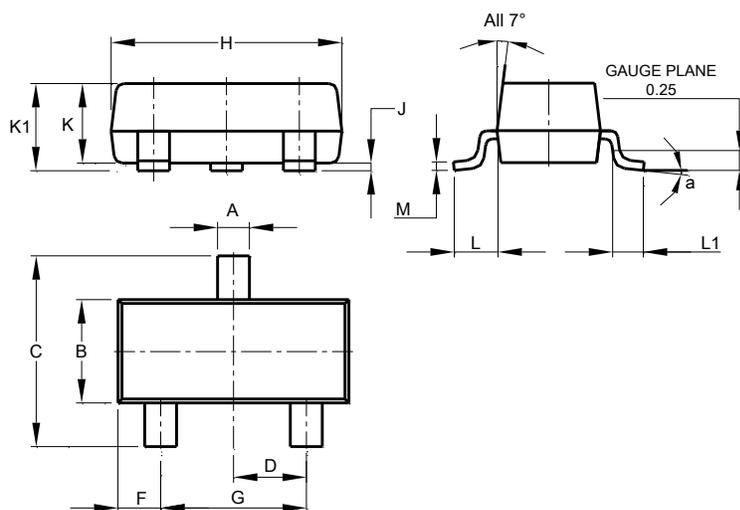
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	V <sub>I(OFF)</sub>	-0.5	-1.1	—	V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	V <sub>I(ON)</sub>	—	-1.9	-3		V <sub>O</sub> = -0.3V, I <sub>O</sub> = -2mA
Output Voltage	V <sub>O(ON)</sub>	—	-0.1	-0.3	V	I <sub>O</sub> /I <sub>I</sub> = -10mA/-0.5mA
Input Current	I <sub>I</sub>	—	—	-0.18	mA	V <sub>I</sub> = -5V
Output Current	I <sub>O(OFF)</sub>	—	—	-0.5	μA	V <sub>CC</sub> = -50V, V <sub>I</sub> = 0V
DC Current Gain	G <sub>I</sub>	68	—	—	—	V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA
Input Resistor Tolerance	ΔR <sub>1</sub>	-30	—	+30	%	—
Resistance Ratio Tolerance	ΔR <sub>2</sub> /R <sub>1</sub>	-20	—	+20	%	—
Gain-Bandwidth Product (Note 7)	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = -5mA, f = 100MHz

Note: 7. Transistor - For Reference Only.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

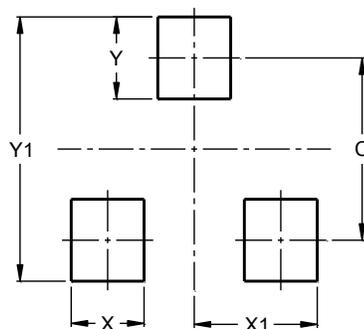


## Package Outline Dimensions

**SOT23**


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

**SOT23**


Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9